



INTELLECTUAL PROPERTY
402-391-4448

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IFW #

JAMES D. WELCH
ATTORNEY AT LAW
PROFESSIONAL ENGINEER

10328 PINEHURST AVE.
OMAHA, NEBRASKA 68124

October 1, 2004

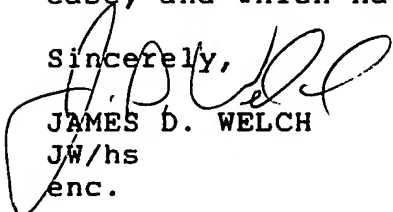
Parsons Hsue and De LLP
655 Montgomery St.
San Francisco, CA 94111

RE: OPPOSITION TO PUBLISHED APPLICATION OF NIKOONAHAD ET AL.
TITLED "OPTICAL SYSTEM FOR MEASURING SAMPLES USING SHORT
WAVELENGTH RADIATION";
SERIAL NO.: 10/718,126;
FILE DATE: NOV. 19, 2003;
PUB. NO.: US2004/0150820.

Dear Sirs;

Enclosed please find copies of materials we feel should be
considered by the Examiner during Prosecution of the identified
case, and which have been provided to the Patent Office.

Sincerely,


JAMES D. WELCH
JW/hs
enc.



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Commissioner for Patents
Box: 1450
Alexandria, AV 22313-1450

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Dear Sir;

Please find enclosed a Check for \$180.00 and Ten (10)
Publications which we feel the Examiner should consider in the
Examination.

ARTICLES:

"OPTICAL METROLOGY ROADMAP FOR THE SEMICONDUCTOR, OPTICAL AND
DATA STORAGE INDUSTRIES", WOOLLAM ET AL., PROC. OF SPIE., VOL
4099, (JULY 2000).

"SPECTROSCOPIC ELLIPSOMETRY FROM THE VACUUM ULTRAVIOLET TO THE
FAR INFRARED:", WOOLLAM ET AL., CHARACTERIZATION AND METROLOGY FOR
ULSI TECHNOLOGY: 2000 INTERNATIONAL CONFERENCE.

"CHARACTERIZATION OF THIN FILMS AND MULTILAYERS IN THE VUV
WAVELENGTH RANGE USING SPECTROSCOPIC ELLIPSOMETRY AND
SPECTROSCOPIC PHOTOMETRY", BOHER ET AL., 157 NM SYMPOSIUM, (MAY
2000).

"MATERIALS CHARACTERIZATION IN THE VACUUM ULTRAVIOLET WITH
VARIABLE ANGLE SPECTROSCOPIC ELLIPSOMETRY", WAGNER ET AL., PHYS.
STAT. SOL. (a) 188, no. 4, (2001).

"SPECTROSCOPIC ELLIPSOMETRY IN THE VACUUM ULTRAVIOLET: 157 NM AND
BELOW", HILFIKER ET AL., (AND RELATED MATERIALS), FUTURE FAB
INTERNATIONAL, (2000).

"157 NM RESIST MATERIALS: PROGRESS REPORT", BRODSKY ET AL., J.
VAC. SCI. TECHNOL. B 18(6) (NOV/DEC 2000).

10/06/2004 SSITHIB1 00000090 10718126

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"IN SITU MONITORING OF GaN METAL-ORGANIC VAPOR PHASE EPITAXY BY SPECTROSCOPIC ELLIPSOMETRY", PETERS, J. APP. PHYS., VOL. 88, NO. 7, (OCT. 2000).

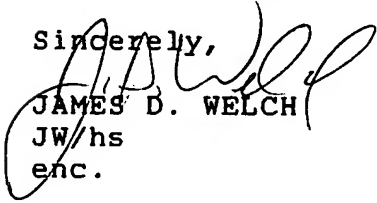
"ORDINARY AND EXTRAORDINARY DIELECTRIC FUNCTIONS OF 4H- AND 6H-SIC FROM 3.5 TO 9.0 EV", LINDQUIST ET AL., APP. PHYS. LETT., VOL 78, NO. 18 (APR. 2001).

"PRECISE CHARACTERIZATION OF RESISTS AND THIN GATE DIELECTRICS IN THE VUV RANGE FOR 157 NM LITHOGRAPHY", BOJER ET AL., MAT. RES. SOC. SYMP., VOL 636, (2001).

"FLUOROPOLYMERS FOR 157-NM LITHOGRAPHY: OPTICAL PROPERTIES FROM VUV ABSORBANCE AND ELLIPSOMETRY MEASUREMENTS", FRENCE ET AL., PROC. SPIE, VOL 4000, (JUL. 2000).

I attest that a copy of the accompanying materials was sent to Applicant's Attorney: Parsons Hsue and De LLP, at 655 Montgomery St., San Francisco, CA 94111 with First Class Postage affixed on October 1, 2004.

Sincerely,


JAMES D. WELCH

JW/hs

enc.